

Docket: TSMC 98 - 262
S/N: 09/325,951

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Washington, D.C. 20231

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TECHNOLOGY CENTER 2800

George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

Subject:

Serial No.: 09/325,951	Filed: 06/04/99
Inventor: Min-Hsiung Chiang	
Title: Method For Forming High Purity Silicon Oxide Field Oxide Isolation Region	
Group Art Unit: 2812	Examiner: Pompey, R. E.
Attorney Docket: TSMC 98 - 262	

RESPONSE TO PATENT OFFICE ACTION


Dear Sir:

In response to the Final office action dated 06/14/02 and as a Preliminary Amended to the Request for Continued Examination filed herewith, please consider the following remarks:

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patent and Trademarks, Washington, D.C. 20231, on October 16, 2002.

Signature/Date


Stephen B. Hckerman, Reg # 37,761
10/15/02

Charge to Deposit Account

The Commissioner is hereby authorized to charge payment of the fee of \$_____ associated with this communication, or credit any overpayment, to Deposit Account No. 19-0033. The Commissioner is also authorized to charge any additional fee under 37 CFR §1.16 and 1.17 to this Deposit Account. A duplicate copy of this sheet is enclosed. The Commissioner is hereby authorized to charge payment of any additional fees involved with added Claims and the like to Deposit Account No. 19-0033.

Respectively submitted,

10/15/02

Date



George O. Saile; or

Stephen B. Ackerman